# **DMG90401**

# Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For general amplification
DMG50401 in SSMini6 type package

#### ■ Features

- $\bullet$  High forward current transfer ratio  $h_{\text{FE}}$  with excellent linearity
- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant
   (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

#### ■ Marking Symbol: A9

#### ■ Basic Part Number

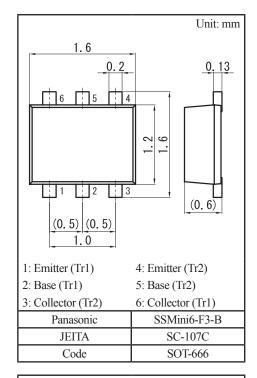
DSC2001 + DSA2001 (Individual)

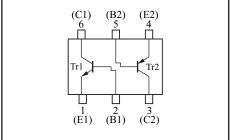
#### ■ Packaging

DMG904010R Embossed type (Thermo-compression sealing): 8 000 pcs / reel (standard)

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
	Collector current	$I_{C}$	100	mA
	Peak collector current	I <sub>CP</sub>	200	mA
Tr2	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
	Collector current	$I_{C}$	-100	mA
	Peak collector current	I <sub>CP</sub>	-200	mA
	Total power dissipation	P <sub>T</sub>	125	mW
Overall	Junction temperature	$T_j$	150	°C
	Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C





## ■ Electrical Characteristics $T_a = 25$ °C±3°C

## • Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CB} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		1.5		pF

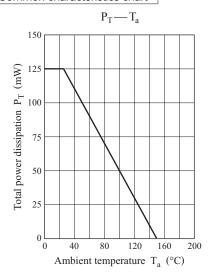
 $Note)\ Measuring\ methods\ are\ based\ on\ JAPANESE\ INDUSTRIAL\ STANDARD\ JIS\ C\ 7030\ measuring\ methods\ for\ transistors.$ 

#### • Tr2

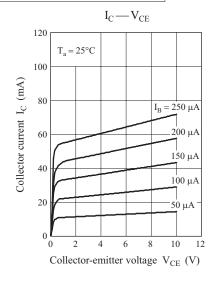
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10  \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.2	-0.5	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_C = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

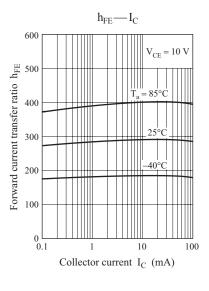
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

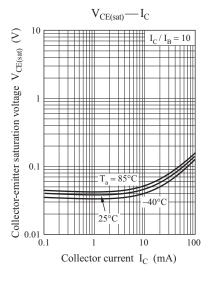
#### Common characteristics chart

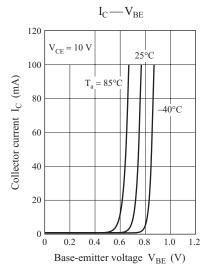


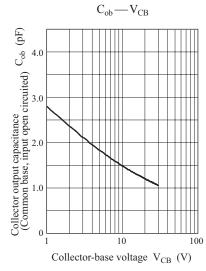
#### Characteristics charts of Tr1

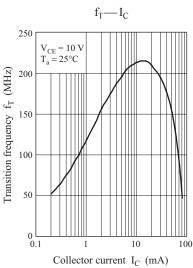




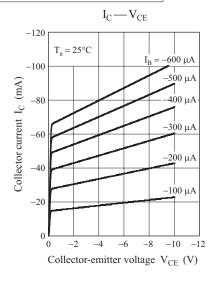


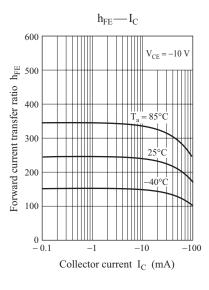


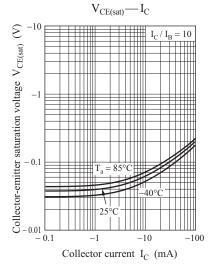


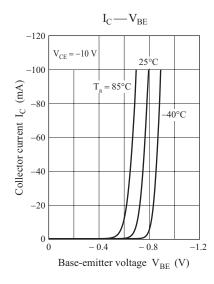


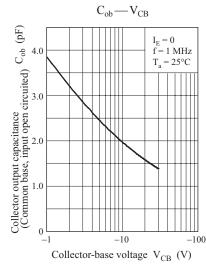
#### Characteristics charts of Tr2

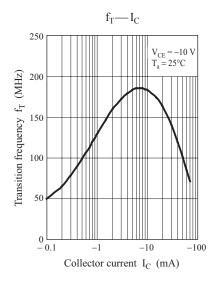






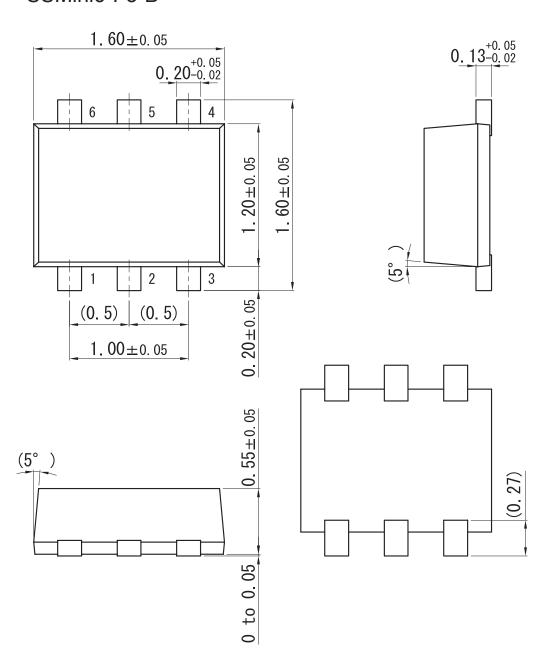




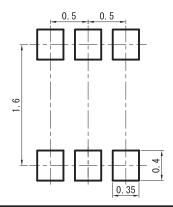


# SSMini6-F3-B

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm)



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